

Press Pack IEGT Silicon N-Channel IEGT

# ST1000GXH35

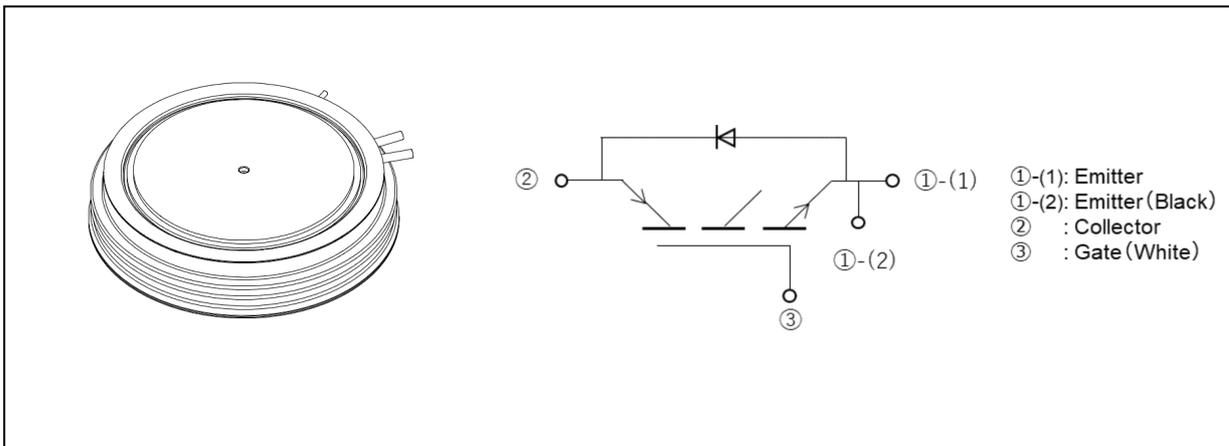
## 1. Applications

- Electric power transmission and distribution
- Motor Controllers
- High-Power Switching

## 2. Features

- (1) High reliability due to hermetic sealing structure.
- (2) Double side cooling type.

## 3. Packaging and Internal Circuit



Start of commercial production  
2024-02

### 4. Absolute Maximum Ratings (Note) ( $T_c = 25\text{ °C}$ , unless otherwise specified)

Characteristics	Symbol	Note	Test Condition	Rating	Unit
Collector-emitter voltage	$V_{CES}$			4500	V
Gate-emitter voltage	$V_{GES}$			$\pm 20$	V
Collector current (DC)	$I_C$		$T_f = 108\text{ °C}$	1000	A
Collector current (pulsed)	$I_{CP}$	(Note 1)		2000	A
Diode forward current (DC)	$I_F$		$T_f = 15\text{ °C}$	1000	A
Diode forward current (pulsed)	$I_{FP}$	(Note 1)		2000	A
Non-repetitive peak forward surge current	$I_{FSM}$		10 ms half-sine wave, $V_R = 0V$ , $T_j = 150\text{ °C}$	6	kA
Collector power dissipation	$P_C$	(Note 2)	Transistor part, $T_f = 25\text{ °C}$	8928	W
Power dissipation	$P_D$	(Note 2)	Diode part, $T_f = 25\text{ °C}$	3571	W
Junction temperature	$T_j$			-40 to 150	$^{\circ}C$
Operating junction temperature	$T_{j(opr)}$			-40 to 125	$^{\circ}C$
Storage temperature	$T_{stg}$			-40 to 125	$^{\circ}C$
Mounting force	—			28 to 35	kN

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width and repetition rate should be such that junction temperature ( $T_j$ ) does not exceed maximum  $T_j$  rating.

Note 2: Refer to the application notes.

### 5. Thermal Characteristics (Note)

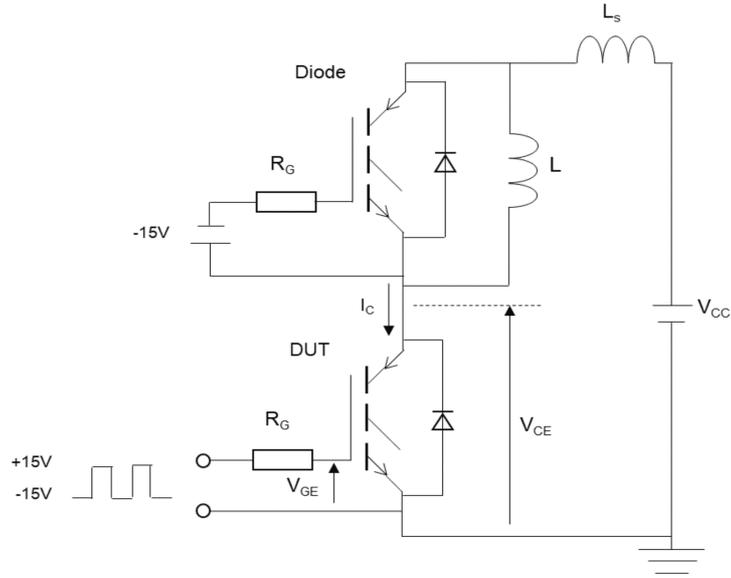
Characteristics	Symbol	Note	Test Condition		Max	Unit
Thermal resistance (junction-to-fin)	$R_{th(j-f)}$	(Note 3)	Transistor part	Double side	14.0	K/kW
Thermal resistance (junction-to-fin)	$R_{th(j-f)}$	(Note 3)	Diode part	Double side	35.0	K/kW

Note: Customers must also refer to and comply with the latest versions of all relevant TOSHIBA information, including without limitation, this document, the specifications, the data sheets and application notes for Product and the precautions and conditions set forth in the "TOSHIBA Semiconductor Reliability Handbook" and the instructions for the application with which the Product will be used with or for.

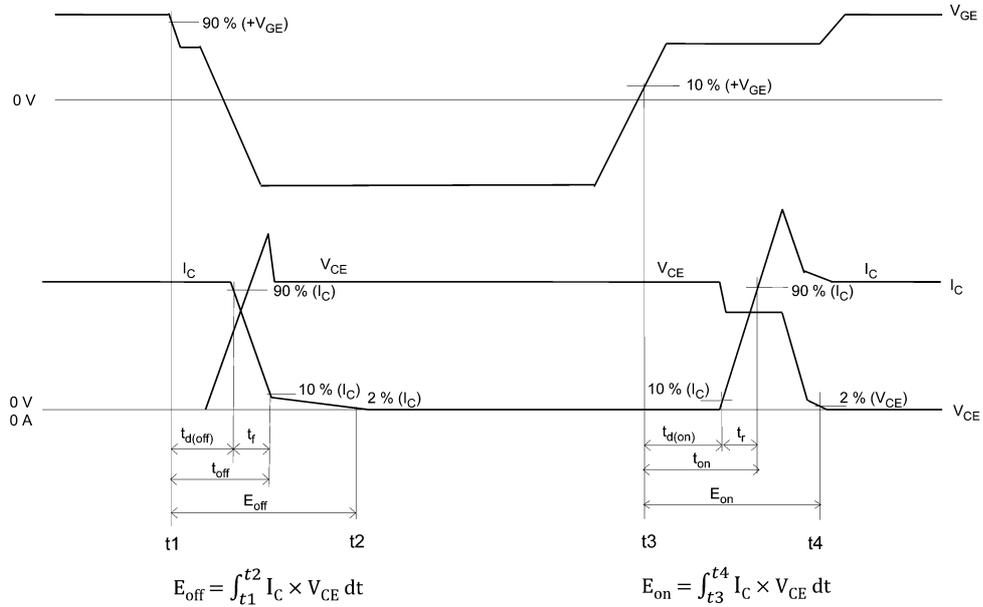
Note 3: Conductive thermal compound is added.

### 6. Electrical Characteristics

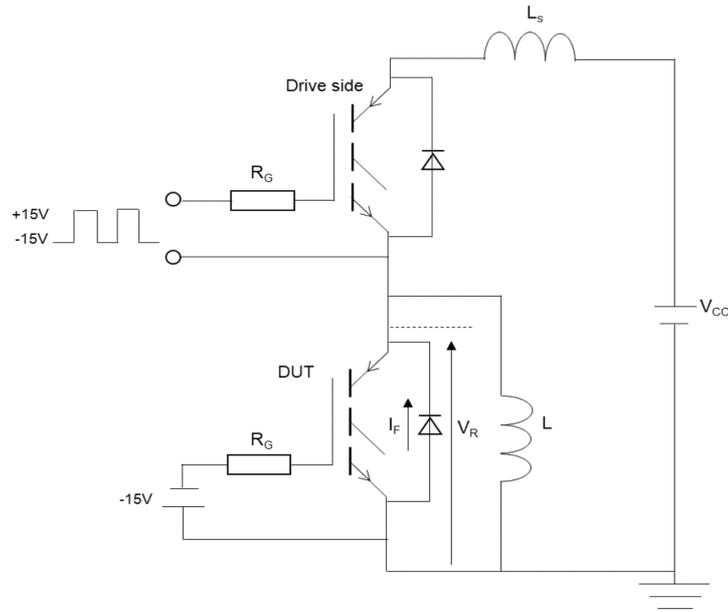
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate-emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$ , $V_{CE} = 0\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	—	—	$\pm 100$	nA
Collector-emitter cut-off current	$I_{CES}$	$V_{CE} = 4500\text{ V}$ , $V_{GE} = 0\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	—	—	0.1	mA
Gate-emitter cut-off voltage	$V_{GE(off)}$	$I_C = 1.0\text{ A}$ , $V_{CE} = 5\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	6.70	7.20	7.70	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1000\text{ A}$ , $V_{GE} = 15\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$	—	2.05	—	V
		$I_C = 1000\text{ A}$ , $V_{GE} = 15\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	—	2.50	2.95	
Input capacitance	$C_{ies}$	$V_{CE} = 10\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 100\text{ kHz}$ , $T_j = 25\text{ }^\circ\text{C}$	—	145	—	nF
Switching time (turn-on delay time)	$t_{d(on)}$	$V_{CC} = 2800\text{ V}$ , $I_C = 1000\text{ A}$ , $V_{GE} = \pm 15\text{ V}$ , $R_{G(on)} = 5.6\text{ }\Omega$ , $R_{G(off)} = 91\text{ }\Omega$ , $T_j = 150\text{ }^\circ\text{C}$ , Diode side: ST1000GXH35	—	0.36	—	$\mu\text{s}$
Switching time (rise time)	$t_r$	$R_{G(off)} = 91\text{ }\Omega$ , $T_j = 150\text{ }^\circ\text{C}$ , Diode side: ST1000GXH35	—	0.26	—	$\mu\text{s}$
Switching time (turn-on time)	$t_{on}$	Diode side: ST1000GXH35	—	0.62	—	$\mu\text{s}$
Switching time (turn-off delay time)	$t_{d(off)}$	$T_j = 150\text{ }^\circ\text{C}$	—	9.80	—	$\mu\text{s}$
Switching time (fall time)	$t_f$	(Inductive load, $L_S \approx 300\text{ nH}$ ) See Fig. 6.1 and Fig. 6.2	—	2.25	—	$\mu\text{s}$
Switching time (turn-off time)	$t_{off}$		—	12.05	—	$\mu\text{s}$
Forward voltage	$V_F$	$I_F = 1000\text{ A}$ , $T_j = 25\text{ }^\circ\text{C}$	—	2.95	—	V
		$I_F = 1000\text{ A}$ , $T_j = 150\text{ }^\circ\text{C}$	—	3.10	3.85	
Reverse recovery current	$I_{rr}$	$V_{CC} = 2800\text{ V}$ , $I_F = 1000\text{ A}$ , $V_{GE} = -15\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ Drive side: ST1000GXH35	—	1250	—	A
Reverse recovery time	$t_{rr}$	$di/dt \approx 3000\text{ A}/\mu\text{s}$ , $T_j = 150\text{ }^\circ\text{C}$ (Inductive load, $L_S \approx 300\text{ nH}$ ) See Fig. 6.3 and Fig. 6.4	—	1.06	—	$\mu\text{s}$
Turn-on switching loss	$E_{on}$	$V_{CC} = 2800\text{ V}$ , $I_C = 1000\text{ A}$ , $V_{GE} = \pm 15\text{ V}$ , $R_{G(on)} = 5.6\text{ }\Omega$ , $R_{G(off)} = 91\text{ }\Omega$ , $T_j = 150\text{ }^\circ\text{C}$ , Diode side: ST1000GXH35	—	3.75	—	J
Turn-off switching loss	$E_{off}$	$T_j = 150\text{ }^\circ\text{C}$ (Inductive load, $L_S \approx 300\text{ nH}$ ) See Fig. 6.1 and Fig. 6.2	—	5.25	—	J
Reverse recovery loss	$E_{rr}$	$V_{CC} = 2800\text{ V}$ , $I_F = 1000\text{ A}$ , $V_{GE} = -15\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ Drive side: ST1000GXH35 $di/dt \approx 3000\text{ A}/\mu\text{s}$ , $T_j = 150\text{ }^\circ\text{C}$ (Inductive load, $L_S \approx 300\text{ nH}$ ) See Fig. 6.3 and Fig. 6.4	—	1.70	—	J
Short-circuit pulse width	$t_{psc}$	$V_{CC} = 3400\text{ V}$ , $V_{GE} = \pm 15\text{ V}$ , $R_{G(on)} = 5.6\text{ }\Omega$ , $R_{G(off)} = 91\text{ }\Omega$ , $L_S \approx 150\text{ nH}$ , $T_j = 125\text{ }^\circ\text{C}$	—	—	10	$\mu\text{s}$



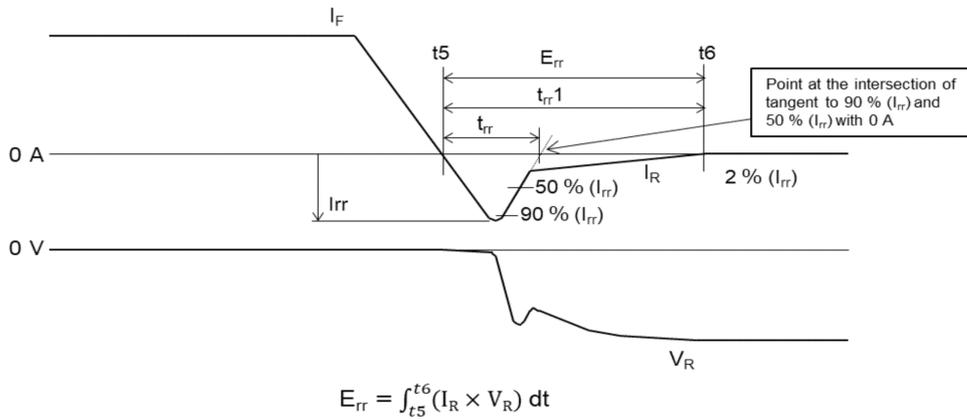
**Fig. 6.1 Test Circuit (Transistor part)**



**Fig. 6.2 Timing Chart (Transistor part)**

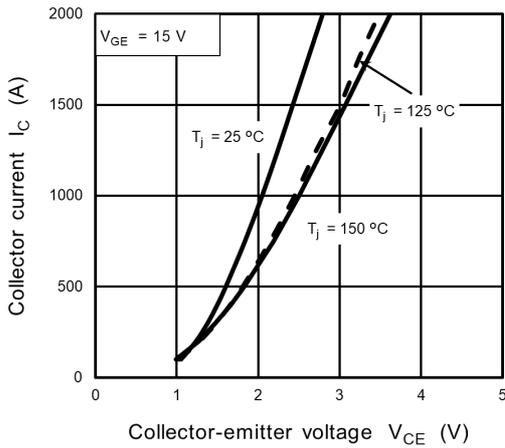


**Fig. 6.3 Test Circuit (Diode part)**

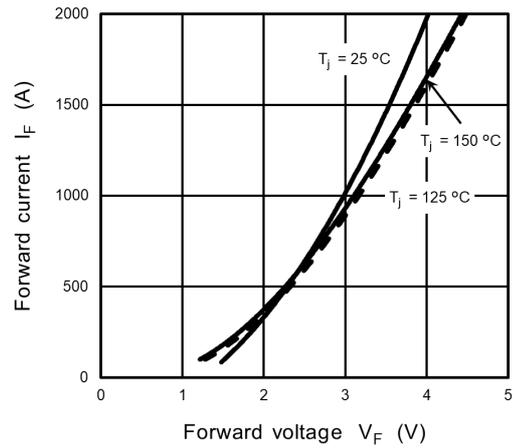


**Fig. 6.4 Timing Chart (Diode part)**

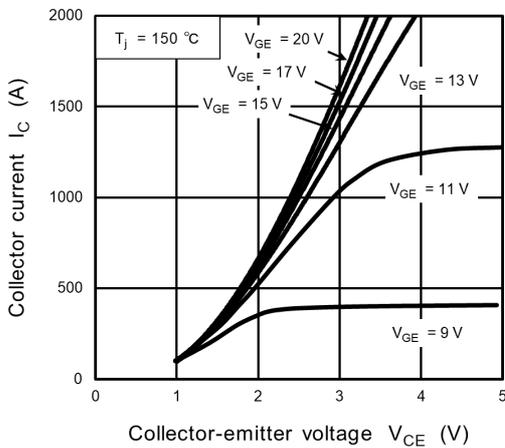
### 7. Characteristics Curves (Note)



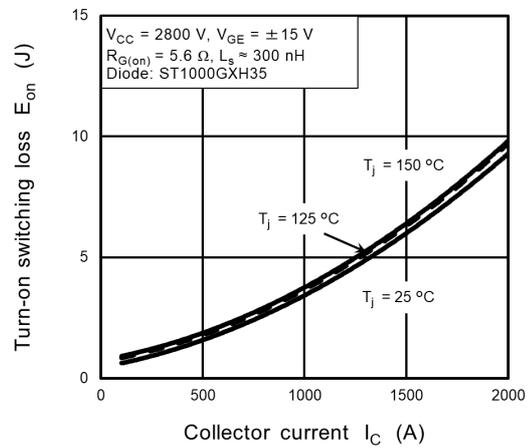
**Fig. 7.1**  $I_C - V_{CE}$



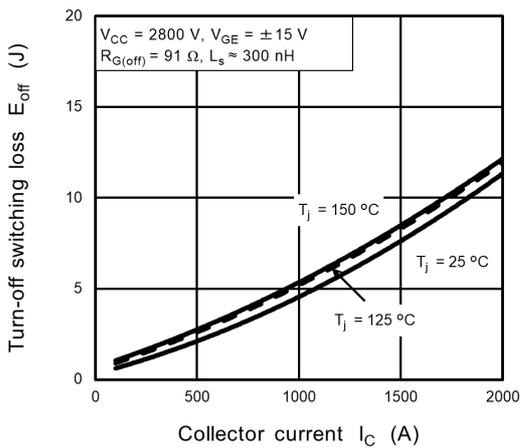
**Fig. 7.2**  $I_F - V_F$



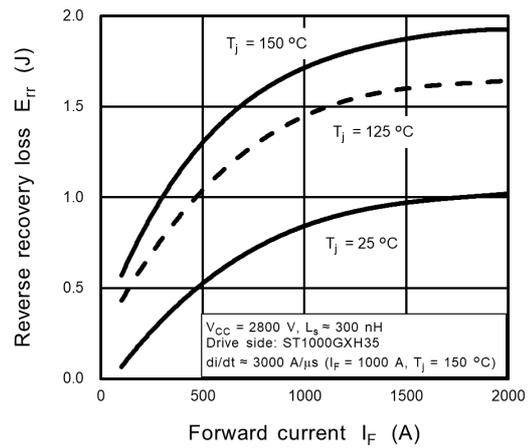
**Fig. 7.3**  $I_C - V_{CE}$



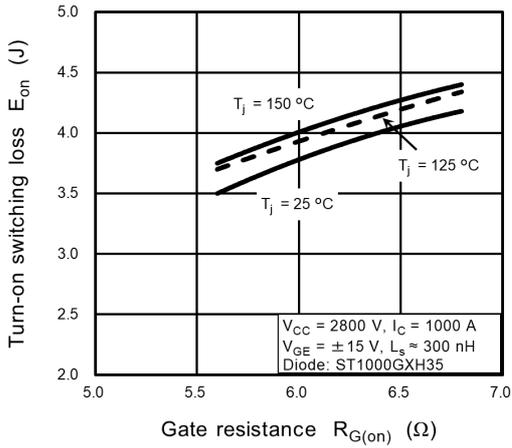
**Fig. 7.4**  $E_{on} - I_C$



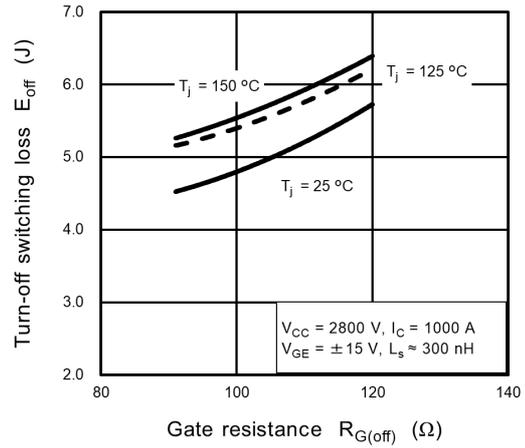
**Fig. 7.5**  $E_{off} - I_C$



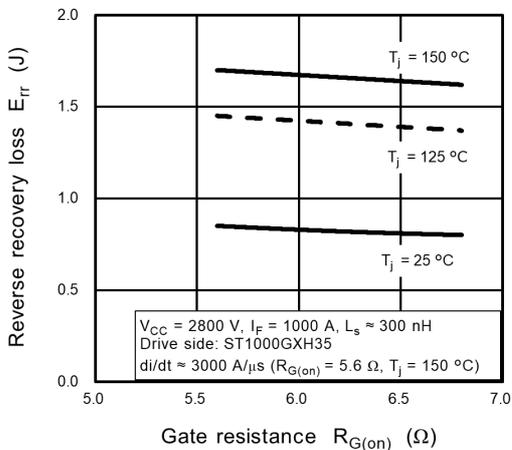
**Fig. 7.6**  $E_{rr} - I_F$



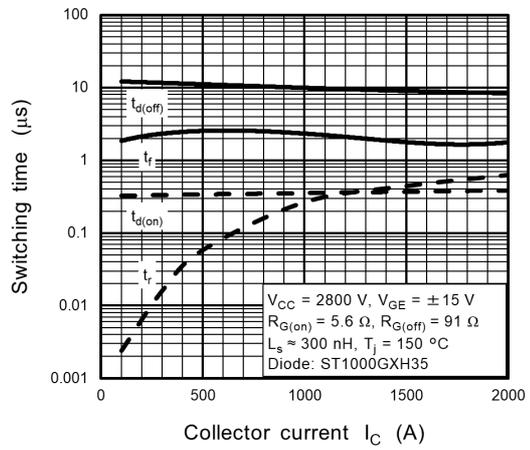
Gate resistance  $R_{G(on)}$  ( $\Omega$ )  
**Fig. 7.7  $E_{on}$  -  $R_{G(on)}$**



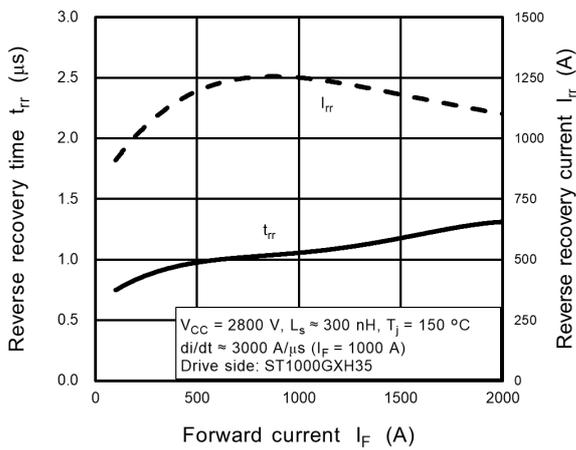
Gate resistance  $R_{G(off)}$  ( $\Omega$ )  
**Fig. 7.8  $E_{off}$  -  $R_{G(off)}$**



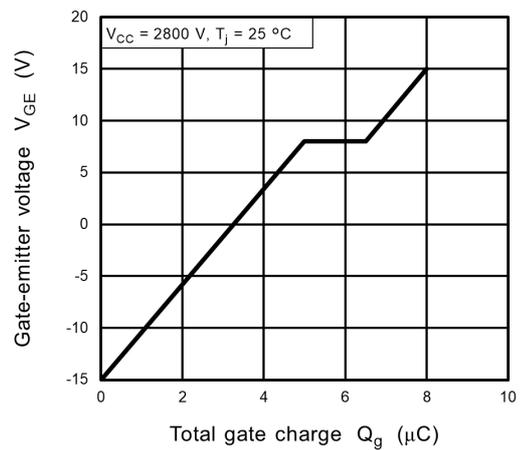
Gate resistance  $R_{G(on)}$  ( $\Omega$ )  
**Fig. 7.9  $E_{rr}$  -  $R_{G(on)}$**



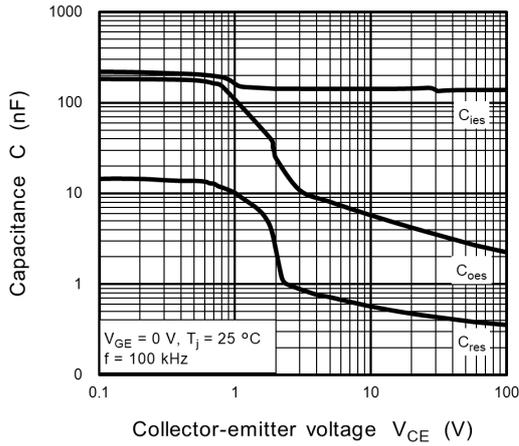
Collector current  $I_C$  (A)  
**Fig. 7.10 Switching time -  $I_C$**



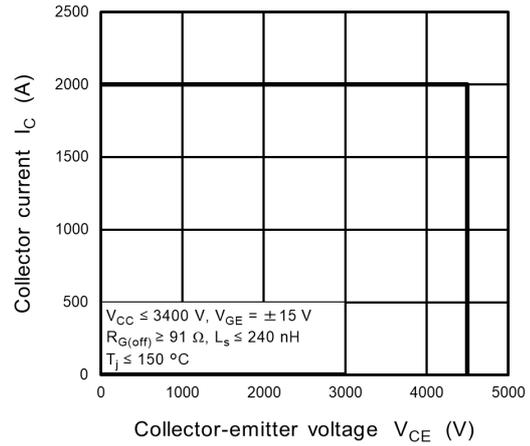
Forward current  $I_F$  (A)  
**Fig. 7.11  $t_{rr}$ ,  $I_{rr}$  -  $I_F$**



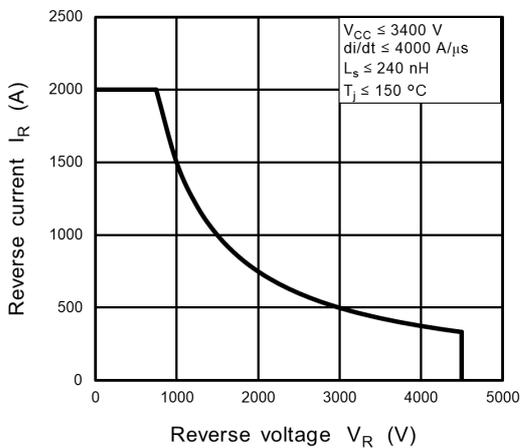
Total gate charge  $Q_g$  ( $\mu C$ )  
**Fig. 7.12  $V_{GE}$  -  $Q_g$**



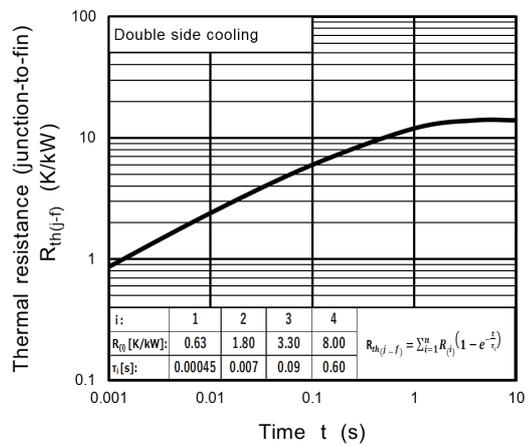
**Fig. 7.13 Capacitance -  $V_{CE}$**



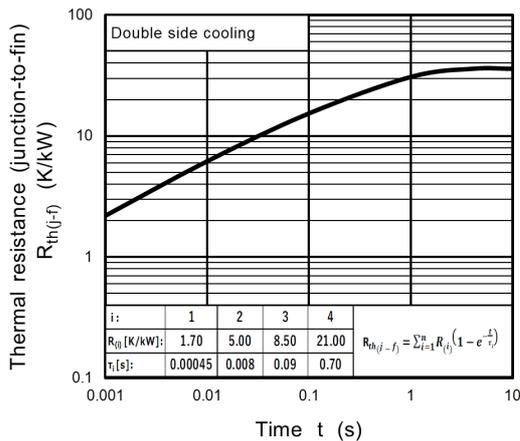
**Fig. 7.14 RBSOA (Guaranteed value)**



**Fig. 7.15 RRSOA (Guaranteed value)**



**Fig. 7.16  $R_{th(j-f)} - t$  (Transistor part)(Guaranteed value)**

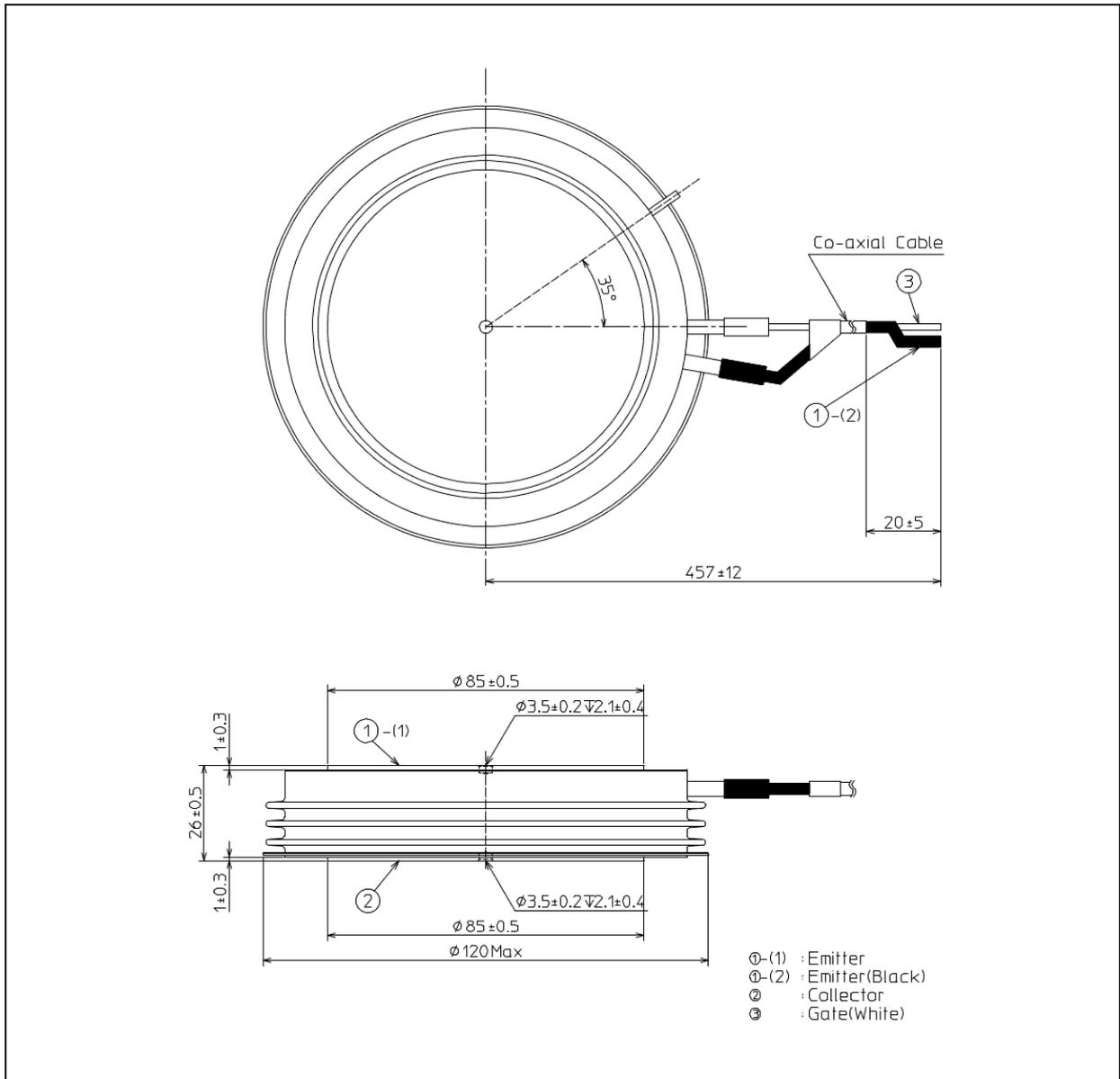


**Fig. 7.17  $R_{th(j-f)} - t$  (Diode part)(Guaranteed value)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### Package Dimensions

Unit: mm



Weight: 1400 g (typ.)

Package Name(s)
TOSHIBA: 2-120B1S

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